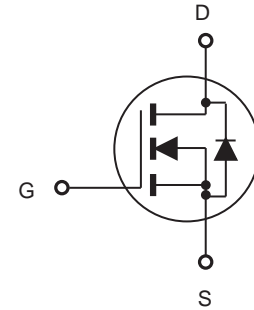


# CEP62A2/CEB62A2

## N-Channel Enhancement Mode Field Effect Transistor

### FEATURES

- 20V, 55A,  $R_{DS(ON)} = 10m\Omega$  @  $V_{GS} = 4.5V$ .  
 $R_{DS(ON)} = 14m\Omega$  @  $V_{GS} = 2.5V$ .
- Super high dense cell design for extremely low  $R_{DS(ON)}$ .
- High power and current handling capability.
- Lead free product is acquired.
- TO-220 & TO-263 package.



### ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous	$I_D$	55	A
Drain Current-Pulsed <sup>a</sup>	$I_{DM}$	220	A
Maximum Power Dissipation @ $T_C = 25^\circ C$ - Derate above $25^\circ C$	$P_D$	54	W
		0.36	W/ $^\circ C$
Operating and Store Temperature Range	$T_J, T_{stg}$	-55 to 175	$^\circ C$

### Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.8	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^\circ C/W$

[查询"CEB62A2"供应商](#)



# CEP62A2/CEB62A2

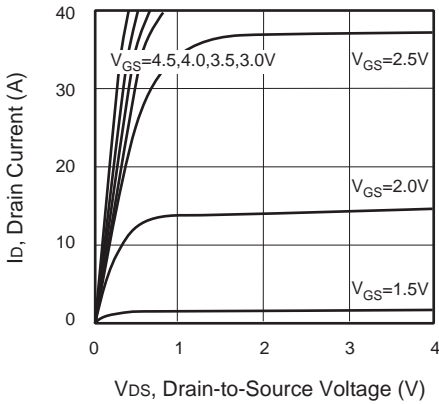


Figure 1. Output Characteristics

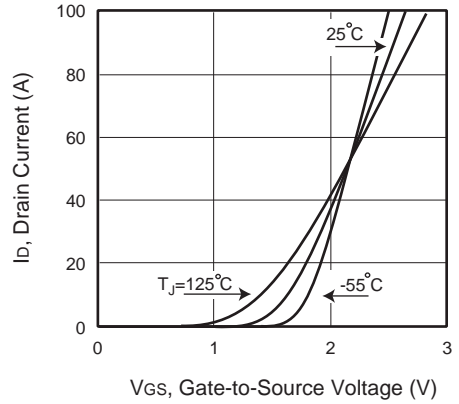


Figure 2. Transfer Characteristics

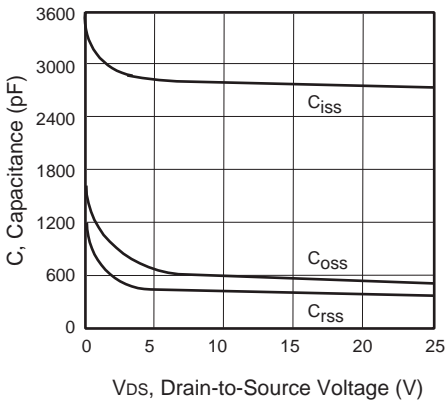


Figure 3. Capacitance

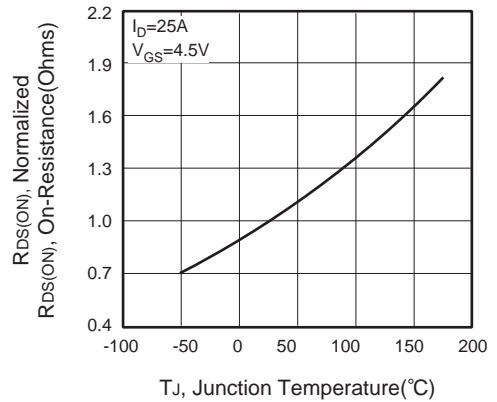


Figure 4. On-Resistance Variation with Temperature

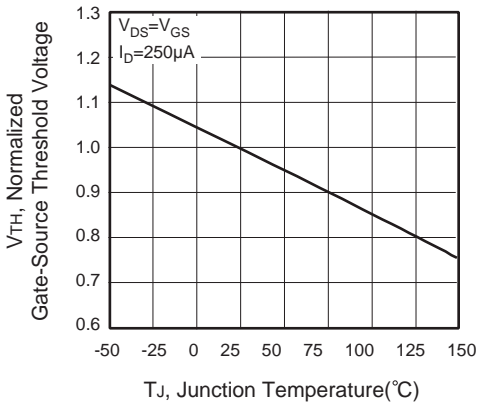


Figure 5. Gate Threshold Variation with Temperature

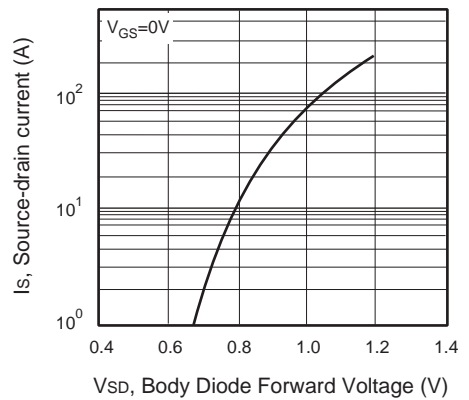


Figure 6. Body Diode Forward Voltage Variation with Source Current



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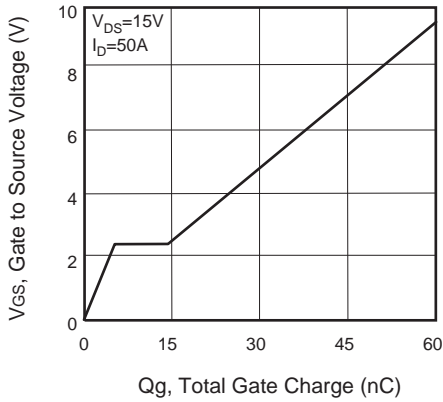


Figure 7. Gate Charge

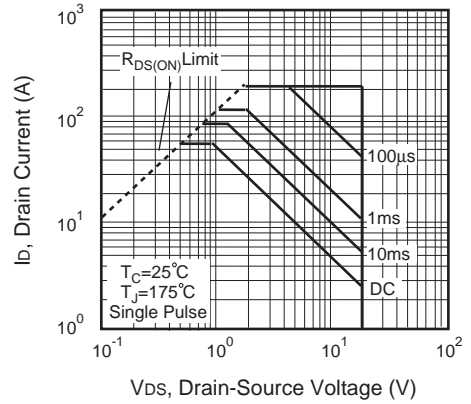


Figure 8. Maximum Safe Operating Area

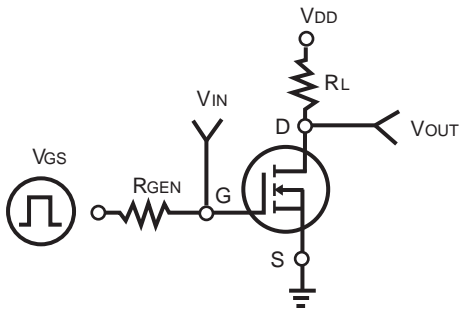


Figure 9. Switching Test Circuit

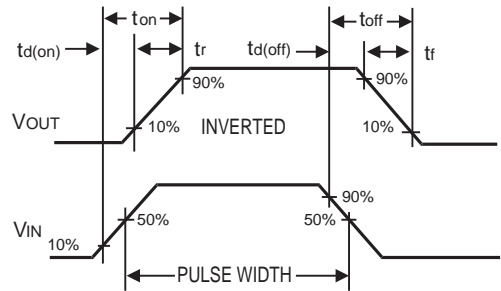


Figure 10. Switching Waveforms

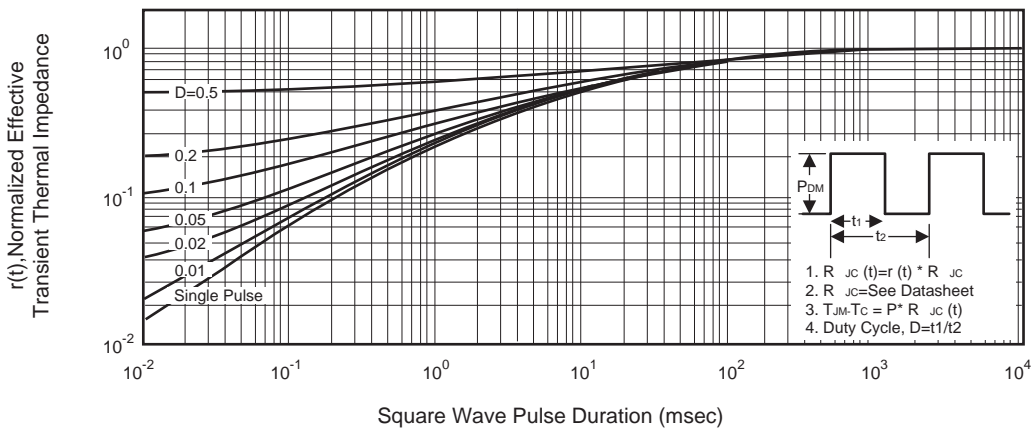


Figure 11. Normalized Thermal Transient Impedance Curve